

SN54HC126, SN74HC126 QUADRUPLE BUS BUFFER GATES WITH 3-STATE OUTPUTS

SCLS103C – MARCH 1984 – REVISED FEBRUARY 1999

- High-Current 3-State Outputs Interface Directly With System Bus or Can Drive up to 15 LSTTL Loads
- Package Options Include Plastic Small-Outline (D), Shrink Small-Outline (DB), and Ceramic Flat (W) Packages, Ceramic Chip Carriers (FK), and Standard Plastic (N) and Ceramic (J) DIPs

description

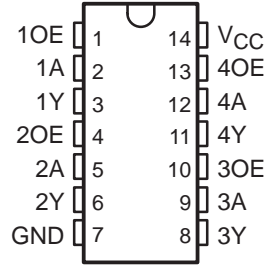
These quadruple bus buffer gates feature independent line drivers with 3-state outputs. Each output is disabled when the associated output-enable (OE) input is low.

The SN54HC126 is characterized for operation over the full military temperature range of -55°C to 125°C . The SN74HC126 is characterized for operation from -40°C to 85°C .

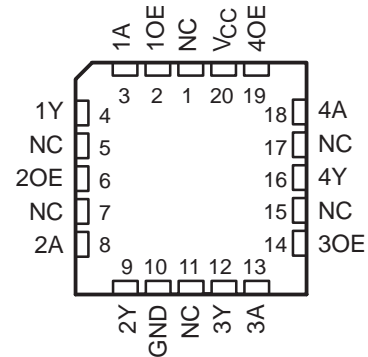
FUNCTION TABLE
(each buffer)

INPUTS		OUTPUT
OE	A	Y
H	H	H
H	L	L
L	X	Z

SN54HC126 . . . J OR W PACKAGE
SN74HC126 . . . D, DB, OR N PACKAGE
(TOP VIEW)

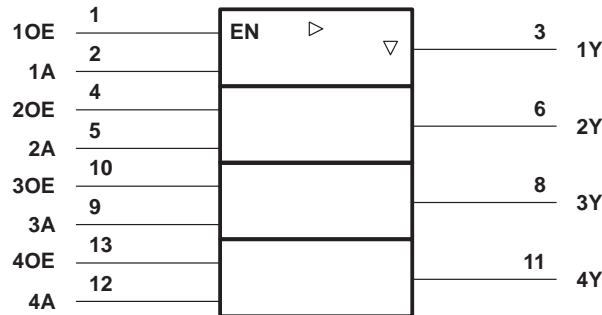


SN54HC126 . . . FK PACKAGE
(TOP VIEW)



NC – No internal connection

logic symbol†



† This symbol is in accordance with ANSI/IEEE Std 91-1984 and IEC Publication 617-12. Pin numbers shown are for the D, DB, J, N, and W packages.



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PRODUCTION DATA information is current as of publication date. Products conform to specifications per the terms of Texas Instruments standard warranty. Production processing does not necessarily include testing of all parameters.

**TEXAS
INSTRUMENTS**

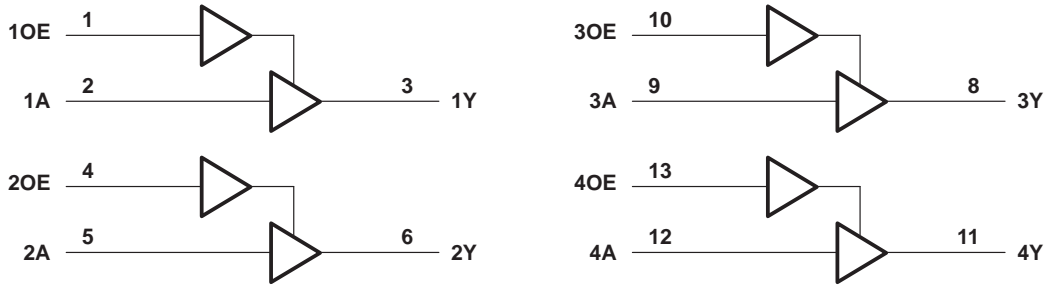
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logic diagram (positive logic)



Pin numbers shown are for the D, DB, J, N, and W packages.

absolute maximum ratings over operating free-air temperature range†

Supply voltage range, V_{CC}	-0.5 V to 7 V
Input clamp current, I_{IK} ($V_I < 0$ or $V_I > V_{CC}$) (see Note 1)	± 20 mA
Output clamp current, I_{OK} ($V_O < 0$ or $V_O > V_{CC}$) (see Note 1)	± 20 mA
Continuous output current, I_O ($V_O = 0$ to V_{CC})	± 35 mA
Continuous current through V_{CC} or GND	± 70 mA
Package thermal impedance, θ_{JA} (see Note 2): D package	127°C/W
DB package	158°C/W
N package	78°C/W
Storage temperature range, T_{stg}	-65°C to 150°C

† Stresses beyond those listed under “absolute maximum ratings” may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated under “recommended operating conditions” is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.

- NOTES: 1. The input and output voltage ratings may be exceeded if the input and output current ratings are observed.
2. The package thermal impedance is calculated in accordance with JESD 51, except for through-hole packages, which use a trace length of zero.

recommended operating conditions (see Note 3)

		SN54HC126			SN74HC126			UNIT
		MIN	NOM	MAX	MIN	NOM	MAX	
V_{CC}	Supply voltage	2	5	6	2	5	6	V
V_{IH}	High-level input voltage	$V_{CC} = 2$ V		1.5	1.5		V	
		$V_{CC} = 4.5$ V		3.15	3.15			
		$V_{CC} = 6$ V		4.2	4.2			
V_{IL}	Low-level input voltage	$V_{CC} = 2$ V		0	0.5	0	0.5	V
		$V_{CC} = 4.5$ V		0	1.35	0	1.35	
		$V_{CC} = 6$ V		0	1.8	0	1.8	
V_I	Input voltage	0		V_{CC}	0		V_{CC}	V
V_O	Output voltage	0		V_{CC}	0		V_{CC}	V
t_t	Input transition (rise and fall) time	$V_{CC} = 2$ V		0	1000	0	1000	ns
		$V_{CC} = 4.5$ V		0	500	0	500	
		$V_{CC} = 6$ V		0	400	0	400	
T_A	Operating free-air temperature	-55		125	-40		85	°C

NOTE 3: All unused inputs of the device must be held at V_{CC} or GND to ensure proper device operation. Refer to the TI application report, *Implications of Slow or Floating CMOS Inputs*, literature number SCBA004.



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electrical characteristics over recommended operating free-air temperature range (unless otherwise noted)

PARAMETER	TEST CONDITIONS		V _{CC}	T _A = 25°C			SN54HC126		SN74HC126		UNIT
				MIN	TYP	MAX	MIN	MAX	MIN	MAX	
V _{OH}	V _I = V _{IH} or V _{IL}	I _{OH} = -20 μA	2 V	1.9	1.998		1.9		1.9	V	
			4.5 V	4.4	4.499		4.4		4.4		
			6 V	5.9	5.999		5.9		5.9		
		I _{OH} = -6 mA	4.5 V	3.98	4.3		3.7		3.84		
		I _{OH} = -7.8 mA	6 V	5.48	5.8		5.2		5.34		
V _{OL}	V _I = V _{IH} or V _{IL}	I _{OL} = 20 μA	2 V		0.002	0.1		0.1		0.1	V
			4.5 V		0.001	0.1		0.1		0.1	
			6 V		0.001	0.1		0.1		0.1	
		I _{OL} = 6 mA	4.5 V		0.17	0.26		0.4		0.33	
		I _{OL} = 7.8 mA	6 V		0.15	0.26		0.4		0.33	
I _I	V _I = V _{CC} or 0		6 V		±0.1	±100		±1000		±1000	nA
I _{OZ}	V _O = V _{CC} or 0		6 V		±0.01	±0.5		±10		±5	μA
I _{CC}	V _I = V _{CC} or 0, I _O = 0		6 V			8		160		80	μA
C _i			2 V to 6 V		3	10		10		10	pF

switching characteristics over recommended operating free-air temperature range, C_L = 50 pF (unless otherwise noted) (see Figure 1)

PARAMETER	FROM (INPUT)	TO (OUTPUT)	V _{CC}	T _A = 25°C			SN54HC126		SN74HC126		UNIT
				MIN	TYP	MAX	MIN	MAX	MIN	MAX	
t _{pd}	A	Y	2 V		47	120		180		150	ns
			4.5 V		14	24		36		30	
			6 V		11	20		31		26	
t _{en}	OE	Y	2 V		57	120		180		150	ns
			4.5 V		16	24		36		30	
			6 V		12	20		31		26	
t _{dis}	OE	Y	2 V		35	120		180		150	ns
			4.5 V		17	24		36		30	
			6 V		15	20		31		26	
t _t		Any	2 V		28	60		90		75	ns
			4.5 V		8	12		18		15	
			6 V		6	10		15		13	



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switching characteristics over recommended operating free-air temperature range, $C_L = 150 \text{ pF}$
(unless otherwise noted) (see Figure 1)

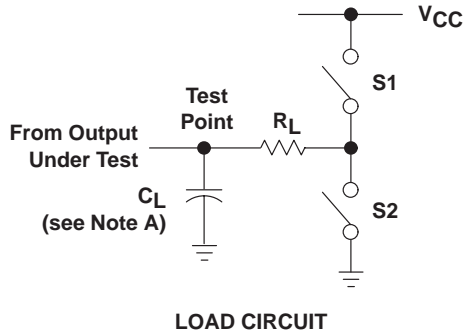
PARAMETER	FROM (INPUT)	TO (OUTPUT)	V_{CC}	$T_A = 25^\circ\text{C}$			SN54HC126		SN74HC126		UNIT
				MIN	TYP	MAX	MIN	MAX	MIN	MAX	
t_{pd}	A	Y	2 V		67	150		225		188	ns
			4.5 V		19	30		45		38	
			6 V		15	25		39		33	
t_{en}	OE	Y	2 V		100	135		202		169	ns
			4.5 V		20	27		40		36	
			6 V		17	23		36		30	
t_t		Any	2 V		45	210		315		265	ns
			4.5 V		17	42		63		53	
			6 V		13	36		53		45	

operating characteristics, $T_A = 25^\circ\text{C}$

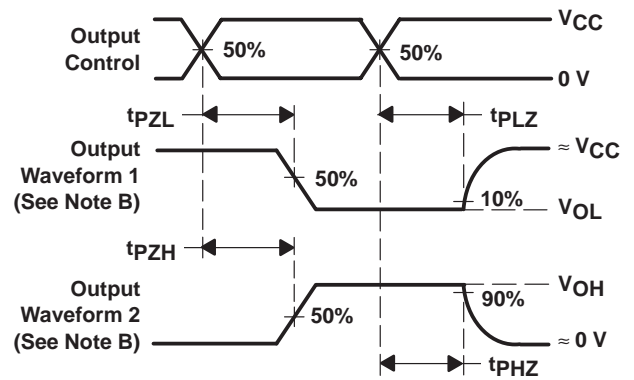
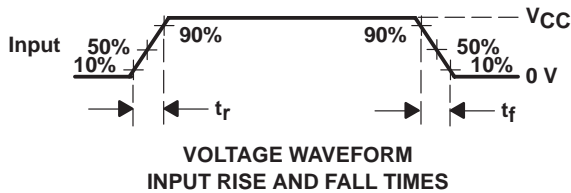
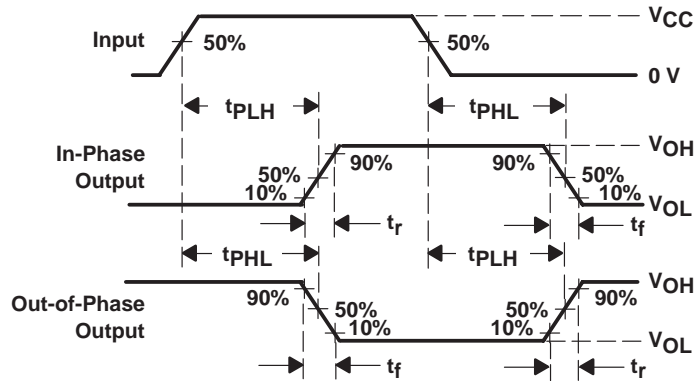
PARAMETER	TEST CONDITIONS	TYP	UNIT
C_{pd} Power dissipation capacitance per gate	No load	45	pF



PARAMETER MEASUREMENT INFORMATION



PARAMETER	R_L	C_L	S1	S2
t_{en}	1 k Ω	50 pF or 150 pF	Open	Closed
			Closed	Open
t_{dis}	1 k Ω	50 pF	Open	Closed
			Closed	Open
t_{pd} or t_t	—	50 pF or 150 pF	Open	Open



- NOTES:
- A. C_L includes probe and test-fixture capacitance.
 - B. Waveform 1 is for an output with internal conditions such that the output is low except when disabled by the output control. Waveform 2 is for an output with internal conditions such that the output is high except when disabled by the output control.
 - C. Phase relationships between waveforms were chosen arbitrarily. All input pulses are supplied by generators having the following characteristics: PRR \leq 1 MHz, $Z_O = 50 \Omega$, $t_r = 6$ ns, $t_f = 6$ ns.
 - D. The outputs are measured one at a time with one input transition per measurement.
 - E. t_{PLZ} and t_{PHZ} are the same as t_{dis} .
 - F. t_{PZL} and t_{PZH} are the same as t_{en} .
 - G. t_{PLH} and t_{PHL} are the same as t_{pd} .

Figure 1. Load Circuit and Voltage Waveforms

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